

N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK Rev. 1 — 20 March 2012 Product data

Product data sheet

#### 1. **Product profile**

### **1.1 General description**

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### **1.3 Applications**

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 100 °C; see <u>Figure 13</u> ; see <u>Figure 14</u>	- :	3.58	4.2	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; see <u>Figure 14</u>		-	2.47	2.9	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 10 A; V <sub>DS</sub> = 20 V;		-	17	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 15; see Figure 16		-	71	-	nC
	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; I <sub>D</sub> = 100 A; $V_{sup}$ ≤ 40 V; unclamped; R <sub>GS</sub> = 50 Ω		-	-	407	mJ

[1] Continuous current rating is limited by package.

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#### N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

### 3. Ordering information

# Table 3. Ordering information Type number Package Name Description Version PSMN2R8-40BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN2R8-40BS	PSMN2R8-40BS

#### N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK

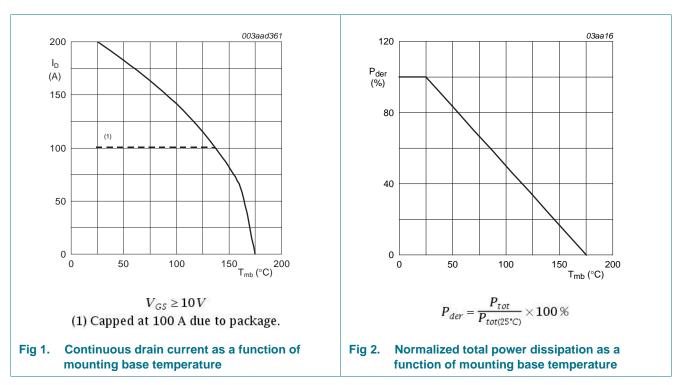
### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

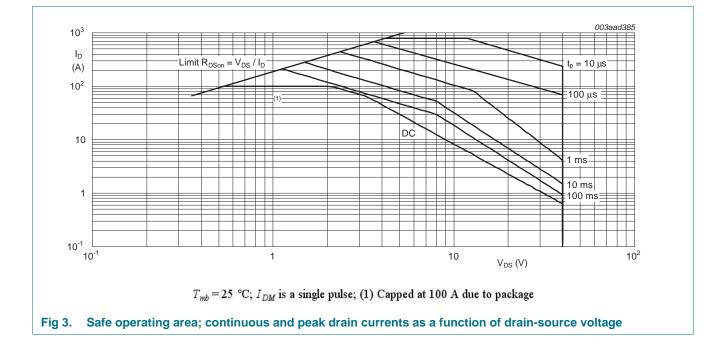
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	[1]	-	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	797	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	211	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	797	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 40$ V; unclamped; $R_{GS}$ = 50 $\Omega$		-	407	mJ

[1] Continuous current rating is limited by package.



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### N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK

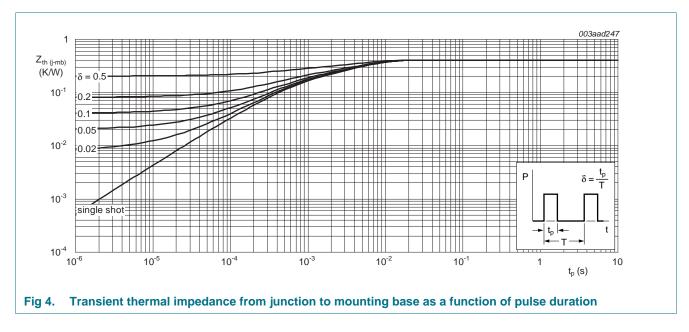


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#### N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK

### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.4	0.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



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N-channel 40 V 2.9 m $\Omega$  standard level MOSFET in D2PAK

### 7. Characteristics

### Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	36	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 12</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2.3	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	10	μA
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 100 °C; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	3.58	4.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ °C};$ see Figure 13; see Figure 14	-	4.94	5.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	2.47	2.9	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	61	-	nC
		$I_D$ = 10 A; $V_{DS}$ = 20 V; $V_{GS}$ = 10 V; see	-	71	-	nC
$Q_{GS}$	gate-source charge	Figure 15; see Figure 16	-	21	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	13	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	8.5	-	nC
$Q_{GD}$	gate-drain charge		-	17	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 10 \text{ A}; V_{DS} = 20 \text{ V}; \text{ see } \frac{\text{Figure } 15}{\text{Figure } 16}$	-	4.7	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4491	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	937	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	464	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	28	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	52	-	ns
t <sub>f</sub>	fall time		-	23	-	ns

PSMN2R8-40BS Product data sheet Symbol

### **PSMN2R8-40BS**

Тур

Max

Unit

#### N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK

Min

#### $I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$ reverse recovery time 47 t<sub>rr</sub> -ns $V_{GS} = 0 V; V_{DS} = 20 V$ $I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$ Qr recovered charge 61 nC --V<sub>GS</sub> = 0 V; V<sub>DS</sub> = 20 V; T<sub>i</sub> = 25 °C 003aad437 003aag678 7000 30 R<sub>DSon</sub> С Ciss $(m\Omega)$ (pF) 25 6000 20 5000 15 C<sub>rss</sub> 4000 10 3000 5 2000 0 $V_{GS}\left(V ight)$ 12 <sup>15</sup> <sub>VGS</sub>(V) <sup>20</sup> 0 3 6 9 0 5 10 $V_{DS} = 0V; f = 1MHz$ $T_j = 25 \,^{\circ}C; \ I_D = 25A$ Input and reverse transfer capacitances as a Drain-source on-state resistance as a function Fig 5. Fig 6.

#### Characteristics ... continued Table 7.

Parameter

Tested to JEDEC standards where applicable.

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of gate-source voltage; typical values

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Source-drain diode  $I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ source-drain voltage

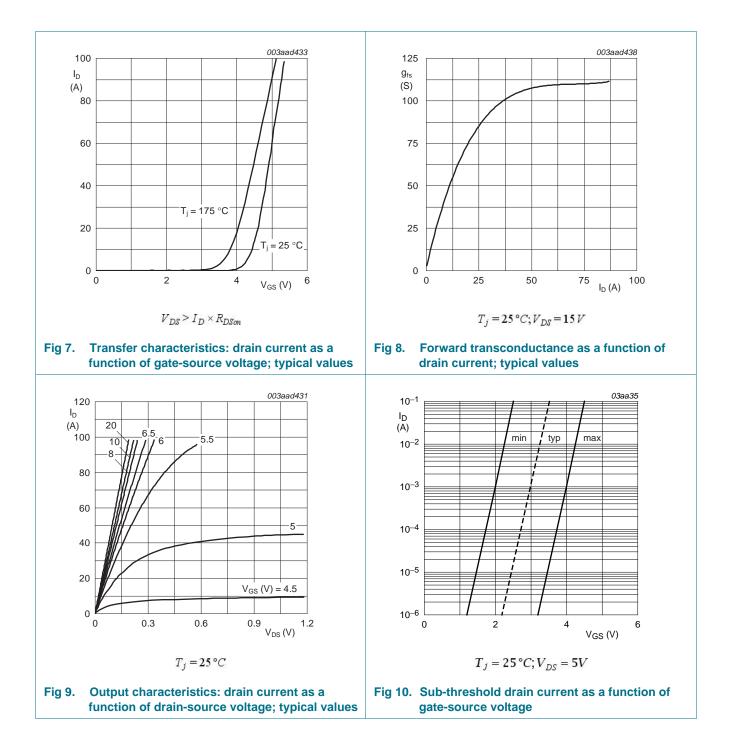
function of gate-source voltage; typical values

V<sub>SD</sub> -0.85 1.2 V see Figure 18

Conditions

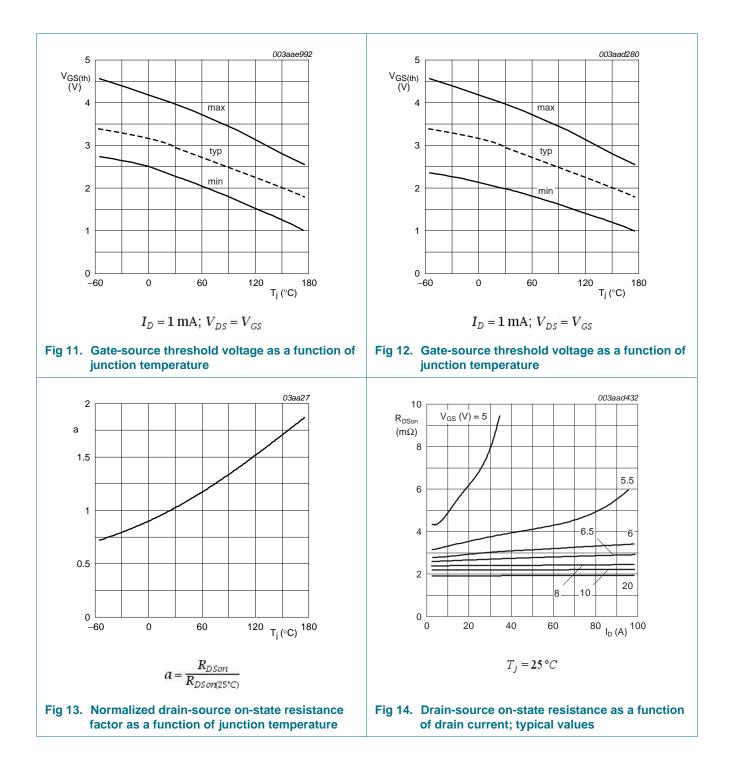
### PSMN2R8-40BS

### N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK



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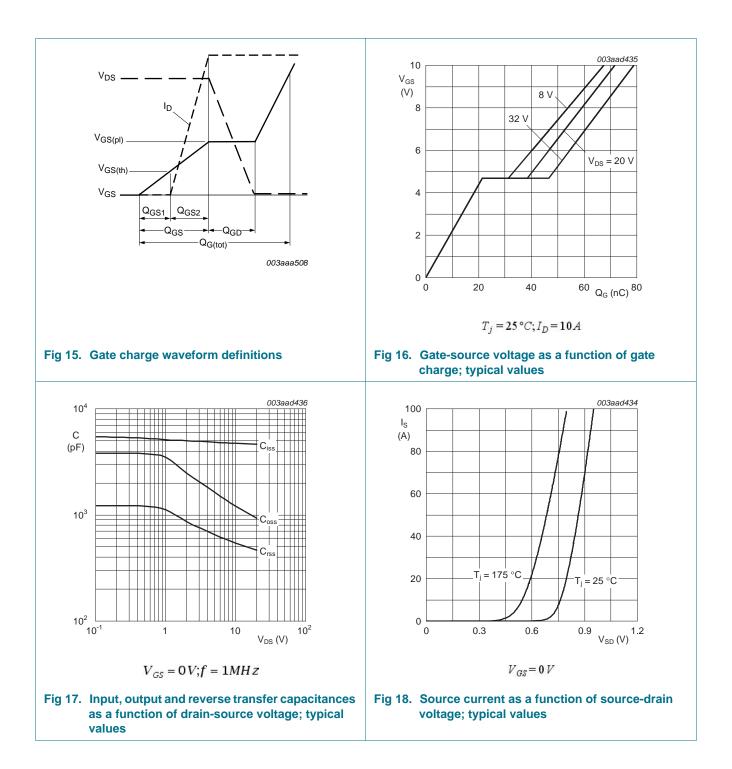
#### N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK



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#### N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK



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#### N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK

### 8. Package outline

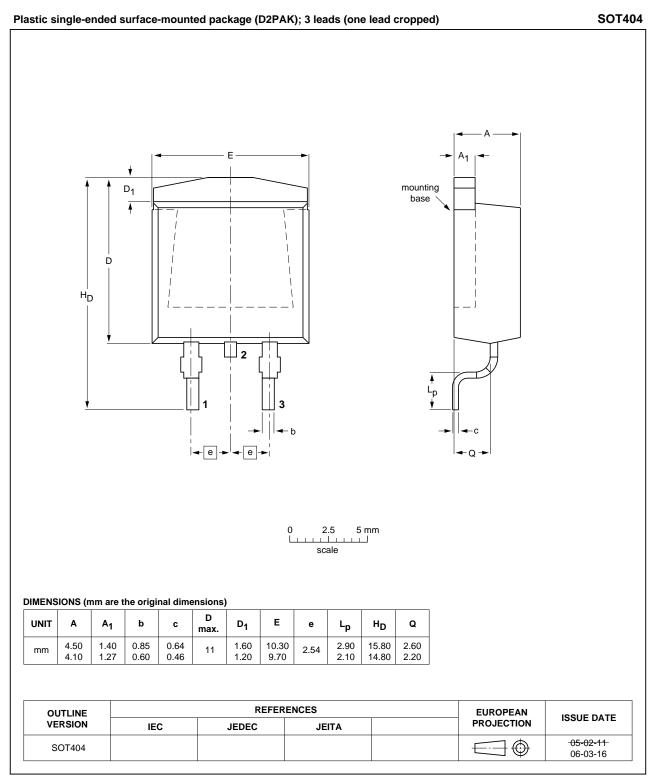


Fig 19. Package outline SOT404 (D2PAK)

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### N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK

### 9. Revision history

Table 8. Revision h	Table 8. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PSMN2R8-40BS v.1	20120320	Product data sheet	-	-		

PSMN2R8-40BS

### **10. Legal information**

### **10.1 Data sheet status**

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Product data sheet

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